

Abstract

~~Device for treating a surface of a substrate, and a plasma source~~

A device [[(1)]] for treating a surface of a substrate ~~(9)~~ comprises includes a treatment chamber [[(3)]] for receiving the substrate therein, and is provided with at least one plasma source [[(13)]] for generating a plasma [[(8)]] which is connected to the treatment chamber [[(3)]] . The plasma source [[(13)]] is provided with an inlet means ~~(11)~~ for admitting at least one reactant into a flow path [[(95)]] of the plasma [[(8)]] . The plasma source ~~(13)~~ comprises includes at least one cathode [[(20)]] and at least one anode [[(5)]] between which a system of cascade plates [[(80)]] is received. The cascade plates [[(80)]] are each provided with a number of passage openings [[(85)]] to provide a number of separate flow paths [[(95)]] for the plasma [[(8)]] . Situated preceding the first cascade plate [[(80)]] of the system there is a common plasma space [[(90)]] which is in open communication with the passage openings [[(85)]] in the cascade plates [[(80)]] of the system.

[[Fig. 1]]